



**MOTOROLA**



actual size

## MC6870, MC6871 series

P/N WILL BE

~~MC6871A1.000 MHz~~

MC6871A1.000 MHz

### Two-Phase Microprocessor Clocks

Designed to drive the Motorola MC6800 MPU

(At least 3 places  
right of decimal pt.)

The *Functional Module* approach to data communications hardware design significantly decreases the time between the "idea" stage and the marketable product.

A fundamental building block in a modular microcomputer system is the 2-phase clock oscillator used to drive the microprocessor. Motorola is uniquely qualified to provide this building block because of expertise in the three relevant fields: oscillator design, quartz crystal technology, and thick film hybrid integrated circuit manufacturing.

This one-of-a-kind expertise has created several clocks designed to drive Motorola's MC6800 Microprocessor. This plug-in unit contains the crystal, the oscillator circuit, the NMOS and TTL drivers, and the waveshaping and interface circuitry; all the components necessary to provide the critical non-overlapping 2-phase waveforms used by the MC6800 MPU.

#### FEATURES

**Clock Module**—Each clock module requires only a single 5 volt power supply. The NMOS outputs can drive highly capacitive loads ranging from 80 pF to 160 pF and meet all MPU input waveshape and timing requirements.

Each TTL output signal leads the  $\phi_2$  NMOS so that additional system device delays can be accommodated. All TTL outputs are buffered so they can drive 5 TTL devices and maintain all output specifications.

Each module is crystal-controlled and is compensated for variations in temperature, voltage, and load. The standard frequency of each model is 1 MHz; however, other frequencies between 250 kHz and 2.5 MHz can be ordered.

**Reliability—Decreased Component Count**—Thick film hybrids offer a reliability advantage that comes primarily from reduced component count and therefore reduced interconnections. Further, the single hermetic seal on the hybrid package reduces the failure rate whereas in a discrete design a separate sealing process with an associated failure rate is needed for each component.

**High Density Packaging**—The hybrid MPU clock allows compact microcomputer design. It takes up only 1.34" x .840" space and has a seated height of .200".

**Ruggedized Design**—Maximum reliability at minimum cost is the result of combining three of Motorola's fields of experience: quartz crystal technology, clock oscillator design, and thick film hybrid integrated circuit manufacturing. Mass automated production techniques assure volume production. Gold plating of all crystals and Class 100 clean room processing testify that no short cuts are taken that might diminish reliability. Environmental testing proves the effectiveness of the rugged design for those applications in which shock and vibration are likely hazards.

**Complete Process Control**—Motorola is the only totally integrated manufacturer of quartz frequency control devices; full control of all processes from growing, sawing, lapping, and finishing quartz to combining it with other components into an electronic product—the MC6870A, MC6871A, and MC6871B MPU clocks.

**Volume Production**—Production facilities are oriented to mass automated production techniques. And, if required, capital for expansion is available to meet even greater requirements.

#### environmental specifications

**Temperature Cycle:**  $\pm 5$  ppm max., 0 to 120°C, 3 cycles, 2 hrs. max. each,  $\pm 2^\circ\text{C}$  ref.

**Shock:** 1000G's 0.35 millisecond,  $\frac{1}{2}$  sine wave, 3 shocks each plane

**Vibration:** 10-55 Hz, .060" D.A.; 55-2000Hz, 35 G's. Duration Time—12 Hours

**Humidity:** 85% Rel. Humidity, @  $+85^\circ\text{C}$ , 250 Hours

#### mechanical specifications

**Gross Leak Test:** All units 100% leak tested in de-ionized  $\text{H}_2\text{O}$ .

**Hermetic Sealed Package:** Mass spectrometer leak rate less than  $2 \times 10^{-8}$  atmos. cc/sec. of helium.

**Seal Strength:** 20 lbs. max. force perpendicular to top and bottom.

**Pin Material:** Phosphor bronze,  $\frac{1}{4}$  hard, Grade A .00003" thick gold flash finish.

**Bend Test:** Will withstand maximum bend of  $90^\circ$  reference to base for 1 bend.

**Marking Ink:** Epoxy, heat cured

**Solvent Resistance:** Isopropyl Alcohol, Trichloroethane Freon TMC. No marking or seal destruction. Dipped 1 minute @  $+25^\circ\text{C}$   $\pm 5^\circ\text{C}$  in solvent.

Note: (1) Unit can be cleaned by only one type solvent listed.

Note: (2) Ultrasonic degreaser not to be used unless frequency and vibration of cleaner specified

#### solderability specifications

##### Materials:

1.1 Solder: 60% tin and 40% lead.

1.2 Flux: The flux shall be 25 percent by weight of Grade WW rosin and 75 percent by weight of 99 percent isopropyl alcohol.

##### Procedure:

2.1 Solder Bath: The solder bath shall be maintained at  $232 \pm 6^\circ\text{C}$ .

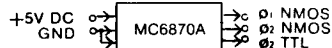
2.2 Solderability: Dip the terminals into the flux to the depth that is to be soldered or to a maximum depth of .025" from the body of the oscillator. Keep them in the flux for at least 5 seconds. Withdraw them from the flux. Dip them immediately into the molten solder to the same depth. Keep them in the molten solder for 2 to 5 seconds. Withdraw them and allow the solder to cool in air.

##### Requirements:

3.1 The terminals are considered solderable and acceptable for electrical connection purposes if 90 percent of the cold solder surface is uniform and free from breaks and pinholes. The other 10 percent of the cooled solder surface may show only pinholes, voids, or rough spots that are not concentrated in one area.

# MC6870A

limited function microprocessor clock  
250 kHz to 2.5 MHz



## specifications

Rating	Symbol	Value	Unit
Supply Voltage	$V_{cc}$	$5.00 \pm 5\%$	Vdc
Operating Temperature Range	$T_A$	0 to +70	°C
Storage Temperature	$T_{stg}$	-55 to +125	°C
Power Supply Drain (max.)	$I_{pd}$	100	mA

ELECTRICAL CHARACTERISTICS ( $V_{cc} = 5.0 \pm 5\%$ ,  $V_{ii} = 0, T_A = 0^\circ$  to  $70^\circ\text{C}$ , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Frequency</b>					
Operating Frequency	$f_c$	.250		2.5	MHz
Frequency stability (inclusive of calibration tolerance at +25°C, operating temperature, input voltage change, load change, aging, shock and vibration)			$\pm .01$		%
<b>NMOS Outputs at 1.0 MHz Operation**</b>					
Pulse Width (meas. at $V_{cc} = -.3\text{V}$ dc level)	$T_{\phi H}$ $T_{\phi L}$	430 450			ns ns
Logic Levels	$V_{OLC}$ $V_{OHC}$	$V_{ii} -.1$ $V_{cc} -.3$	—	$V_{ii} +.3$ $V_{cc} +.1$	Vdc Vdc
Rise and Fall Times	$t_r$ $t_f$	5 5	12 12	50 50	ns ns
*Overshoot/Undershoot Logic "1" Logic "0"	$V_{OS}$	$V_{cc} -.5$ $V_{ii} -.5$		$V_{cc} +.5$ $V_{ii} +.5$	Vdc Vdc
Pulse duration of any overshoot or undershoot	$T_{OS}$			40	ns
Period @ 0.3V dc Level	$t_{cyc}$		1.00		us
Edge Timing @ $V_{cc} = 0.3\text{V}$ dc	$T_X$	940			ns
NMOS Relationship @ +0.5V dc Level	$t_{d1}$ $t_{d2}$	0 0		8.0	us
<b>TTL Outputs</b>					
In ref. to Ø2 NMOS @ 0.3V dc					
Ø2 TTL @ +1.4V dc	$T_A$ $T_H$	15 10	30 25	45 40	ns ns
Logic Levels	$V_{OH}$ $V_{OL}$	2.4	3.2 .3	.4	Vdc Vdc
Rise and Fall Times .4V and 2.4V 2.4V and .4V	$t_r$ $t_f$			15 15	ns ns
Logic "0" Sink (/Gate)	$I_{OL}$			-1.6	mA
Logic "1" Source (/Gate)	$I_{OH}$			+40	uA
Current Output Shorted	$I_{SC}$	-18		-57	mA
<b>Load</b>					
NMOS—Load Capacity Ø1, Ø2	$C_{NMOS}$	80	120	160	pf
TTL—No. of Loads				5	tTL
TTL—Load Capacity	$C_{TTL}$			50	pf

\* Into specified test load

\*\* Apply the following parameters for frequencies other than 1.0 MHz:

$T_{\phi H} = 0.5$  (P-140) ns

$T_{\phi L} = 0.5$  (P-100) ns

$T_X = (P-60)$  ns

where P=desired period of operation in nanoseconds

PIN	CONNECTION
1	GND
3	NC
5	Ø2 TTL
7	$V_{cc}$ (+5VDC)
12	Ø2 NMOS
13	Ø1 NMOS
18	GND
20	NC
22	NC
24	NC

Note: All dimensions are in inches

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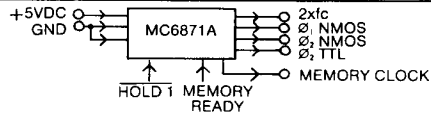
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# MC6871A

full function microprocessor clock  
850 kHz to 2.5 MHz



## specifications

Rating	Symbol	Value	Unit
Supply Voltage	$V_{cc}$	$5.00 \pm 5\%$	Vdc
Operating Temperature Range	$T_A$	0 to +70	°C
Storage Temperature	$T_{stg}$	-55 to +125	°C
Power Supply Drain (max.)	$I_{pd}$	100	mA

ELECTRICAL CHARACTERISTICS ( $V_{cc} = 5.0 \pm 5\%$ ,  $V_{in} = 0, T_A = 0^\circ$  to  $70^\circ\text{C}$ , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Frequency</b>					
Operating Frequency	$f_c$	.850		2.5	MHz
Frequency stability (inclusive of calibration tolerance at +25°C, operating temperature, input voltage change, load change, aging, shock and vibration)			$\pm .01$		%
<b>NMOS Outputs at 1.0 MHz Operation***</b>					
Pulse Width (meas. at $V_{cc} = -3\text{V}$ dc level)	$T_{\phi 1H}$ $T_{\phi 2H}$	430 450			ns ns
Logic Levels	$V_{OLC}$ $V_{OHC}$	$V_{in} - .1$ $V_{cc} - .3$	—	$V_{in} + .3$ $V_{cc} + .1$	Vdc Vdc
Rise and Fall Times	$t_r$ $t_f$	5 5	12 12	50 50	ns ns
*Overshoot/Undershoot Logic "1" Logic "0"	$V_{OS}$	$V_{cc} - .5$ $V_{in} - .5$		$V_{cc} + .5$ $V_{in} + .5$	Vdc Vdc
Pulse duration of any overshoot or undershoot	$T_{OS}$			40	ns
Period @ 0.3V dc Level	$t_{cyc}$		1.00		us
Edge Timing @ $V_{cc} = 0.3\text{V}$ dc	$T_x$	940			ns
NMOS Relationship @ +0.5V dc Level	$t_{d1}$ $t_{d2}$	0 0		8.0	us
<b>TTL Outputs</b>					
In ref. to $\phi_1$ , NMOS @ 0.3V dc					
$\phi_2$ TTL @ 1.4V dc	$T_A$ $T_H$	15 10	30 25	45 40	ns ns
Memory Clock @ 1.4V dc	$T_C$ $T_J$	30 20	50 40	70 60	ns ns
2x $f_c$ @ 1.4V dc	$T_B$	40	80	120	ns
Logic Levels	$V_{OH}$ $V_{OL}$	2.4 .3	3.2 .3	.4	Vdc Vdc
Rise and Fall Times .4V and 2.4V 2.4V and .4V	$t_r$ $t_f$			15 15	ns ns
Logic "0" Sink (/Gate)	$I_{OL}$			-1.6	mA
Logic "1" Source (/Gate)	$I_{OH}$			+40	uA
Current Output Shorted	$I_{SC}$	-18		-57	mA
<b>Load</b>					
NMOS—Load Capacity $\phi_1, \phi_2$	$C_{NMOS}$	80	120	160	pf
TTL—No. of Loads				5	tTL
TTL—Load Capacity	$C_{TTL}$			50	pf
<b>Logic Inputs** ("0" Level Applies HOLD or MEMORY READY)</b>					
Holds $\phi_1$ , NMOS 'High', $\phi_2$ , NMOS 'Low', $\phi_2$ TTL 'Low'	HOLD 1	-2		+4	Vdc
Holds $\phi_1$ , NMOS 'Low', $\phi_2$ , NMOS 'High', $\phi_2$ TTL 'High', and MEMORY CLOCK 'High'	MEM-ORY READY	-2		+4	Vdc

\*Into specified test load

\*\*Must be externally held at "1" level (2.4V min., 5.0V max.) if not used

\*\*\*Apply the following parameters for frequencies other than 1 MHz:

$T_{\phi 1H} = 0.5$  (P-140) ns

$T_{\phi 2H} = 0.5$  (P-100) ns

$T_x = (P-60)$  ns

where P=desired period of operation in nanoseconds

PIN	CONNECTION
1	GND
3	MEMORY CLOCK
5	$\phi_2$ TTL
7	$V_{cc}$ (+5VDC)
12	$\phi_2$ NMOS
13	$\phi_2$ NMOS
18	GND
20	HOLD 1
22	MEMORY READY
24	2x $f_c$

Note: All dimensions are in inches

[illegible]

**TEST CIRCUIT**

POWER SUPPLY  
+ 5 V DC  
GND

MC6871A

1.0μF

1.0μF

MEMORY CLOCK

TTL OUT

RS

CnMOS

02 NCMOS OUT

01 NCMOS OUT

RS

HOLD 1

MEMORY READY

2xlc

CtTL

SCOPE PROBES  
2.5 pF MAX

A  
OSCILLOSCOPE  
TEKTRONIX  
7904 OR EQUIV

B  
100 MHz  
FREQUENCY  
COUNTER  
HP5327C  
OR EQUIV

TO EXTERNAL  
FREQUENCY  
STANDARD

CtTL — MAX CAPACITY 50 pF.

CnMOS — 120 pF ± 40 pF IS THE SPECIFIED MAX. LOAD CAPACITANCE THAT SIMULATES THE MOTOROLA MC6800 MPU INPUT.

\*HOLD AND MEMORY READY MUST BE EXTERNALLY HELD AT "1" LEVEL (2.4VDC MIN., 5.0VDC MAX.) WHEN NOT USED.

RS—(22Ω) SIMULATES REAL PART OF MPU

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## specifications

ELECTRICAL CHARACTERISTICS ( $V_{CC} = 5.0 \pm 5\%$ ,  $V_{in} = 0$ ,  $T_A = 0^\circ$  to  $70^\circ\text{C}$ , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Frequency</b>					
Operating Frequency	$f_c$	250		2.5	MHz
Frequency stability (inclusive of calibration tolerance at +25°C, operating temperature, input voltage change, load change, aging, shock and vibration)			$\pm .01$		%
<b>NMOS Outputs at 1.0 MHz Operation***</b>					
Pulse Width (meas. at $V_{cc} = -3V$ dc level)	$T_{\phi H}$ $T_{\phi L}$	430 450			ns ns
Logic Levels	$V_{OLC}$ $V_{OLHC}$	$V_{IL} - .1$ $V_{IL} - .3$	— —	$V_{IH} + .3$ $V_{CC} + .1$	Vdc Vdc
Rise and Fall Times	$t_r$ $t_f$	5 5	12 12	50 50	ns ns
* Overshoot/Undershoot Logic "1" Logic "0"	$V_{OS}$	$V_{CC} - .5$ $V_{IL} - .5$		$V_{CC} + .5$ $V_{IH} + .5$	Vdc Vdc
Pulse duration of any overshoot or undershoot	$T_{OS}$			40	ns
Period @ 0.3V dc Level	$t_{c,c}$		1.00		us
Edge Timing @ $V_{cc} = 0.3V$ dc	$T_x$	940			ns
NMOS Relationship @ +0.5V dc	$t_{d1}$ $t_{d2}$	0 0		8.0	us
<b>TTL Outputs</b>					
In ref. to $\phi_2$ ; NMOS @ 0.3V dc					
$\phi_2$ TTL @ 1.4V dc	$T_A$ $T_H$	15 10	30 25	45 40	ns ns
$\phi_2$ Ungated @ 1.4V dc	$T_C$ $T_J$	30 20	50 40	70 60	ns ns
2xfc @ 1.4V dc	$T_{\phi}$	40	80	120	ns
<b>Logic Levels</b>	$V_{OH}$ $V_{OL}$	2.4	3.2 .3	.4	Vdc Vdc
Rise and Fall Times .4V and 2.4V 2.4V and .4V	$t_r$ $t_f$			15 15	ns ns
Logic "0" Sink (/Gate)	$I_{OL}$			—1.6	mA
Logic "1" Source (/Gate)	$I_{OH}$			+40	uA
Current Output Shorted	$I_{SC}$	—18		—57	mA
<b>Load</b>					
NMOS—Load Capacity $\phi_1, \phi_2$	$C_{NMOS}$	80	120	160	pf
TTL—No. of Loads				5	ttl
TTL—Load Capacity	$C_{TTL}$			50	pf
<b>Logic Inputs** ("0" Level applies HOLD)</b>					
Holds $\phi_1$ , NMOS 'High', $\phi_2$ , NMOS 'Low', $\phi_2$ TTL 'Low'	HOLD 1	—2		+4	Vdc
Holds $\phi_1$ , NMOS 'Low', $\phi_2$ , NMOS 'High', $\phi_2$ TTL 'High'	HOLD 2	—2		+4	Vdc

**Note: 4xfc available on request**

**Note** All dimensions are in inches

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